

In paper no. 8

L Number	Hits	Search Text	DB	Time stamp
-	10	"5854534" and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 14:49
-	314	flexible.ti. and 257/\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 14:49
-	58	(flexible and substrate).ti. and 257/\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 14:50
-	300	substrate with fold\$3 and 257/\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 14:51
-	0	20020125504.URPN.	USPAT	2002/12/02 15:39
-	8	(US-6469903-\$ or US-6462412-\$ or US-6208521-\$ or US-6121676-\$ or US-5717556-\$).did. or (US-20020114143-\$).did. or (JP-02199859-\$ or JP-63010549-\$).did.	USPAT; US-PGPUB; JPO	2002/12/02 16:27
-	1	jp-06168985-\$).did.	USPAT; US-PGPUB; JPO	2002/12/02 18:26
-	76	memory adj chip with semiconductor with pattern\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/03 13:25
-	2	5776797.pn..	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/03 13:30
-	185	flexible adj substrate with semiconductor and 257/\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/03 13:31
-	23	flexible adj substrate with (conventional\$2 typical\$2 common\$3) with material and 257/\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/03 14:54
-	42700	(257/666-786,797).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/03 14:55
-	0	((257/666-786,797).CCLS.) and flexibe adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/03 14:55
-	396	((257/666-786,797).CCLS.) and flexible adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/03 14:55